ne<mark>x</mark>peria

Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

Instead of <u>http://www.nxp.com</u>, <u>http://www.philips.com/</u> or <u>http://www.semiconductors.philips.com/</u>, use <u>http://www.nexperia.com</u>

Instead of sales.addresses@www.nxp.com or sales.addresses@www.semiconductors.philips.com, use **salesaddresses@nexperia.com** (email)

Replace the copyright notice at the bottom of each page or elsewhere in the document, depending on the version, as shown below:

- © NXP N.V. (year). All rights reserved or © Koninklijke Philips Electronics N.V. (year). All rights reserved

Should be replaced with:

- © Nexperia B.V. (year). All rights reserved.

If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

PNP/PNP double resistor-equipped transistors; R1 = 2.2 kΩ, R2 = open

Rev. 02 — 2 September 2009

Product data sheet

Product profile 1.

1.1 General description

PNP/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages

Product overview Table 1.

Type number	Package		NPN/PNP	NPN/NPN
	NXP	JEITA	complement	complement
PEMB30	SOT666	-	PEMD30	PEMH30
PUMB30	SOT363	SC-88	PUMD30	PUMH30

Reduces component count

and BC857BV

Reduces pick and place costs

Cost-saving alternative for BC857BS

1.2 Features

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design

1.3 Applications

Low current peripheral driver

Control of IC inputs

1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
lo	output current		-	-	-100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ



006aaa268

PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

2. Pinning information

Table 3.	Pinning				
Pin	Description	Simplified outline	Symbol		
1	GND (emitter) TR1				
2	input (base) TR1	6 5 4			
3	output (collector) TR2				
4	GND (emitter) TR2				
5	input (base) TR2				
6	output (collector) TR1	001aab555	R1		
			 1 2 3		

3. Ordering information

Table 4.	Ordering	information
----------	----------	-------------

Type number	Package		
	Name	Description	Version
PEMB30	-	plastic surface-mounted package; 6 leads	SOT666
PUMB30	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Marking code ^[1]
2T
*B2

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

5. Limiting values

Symbol	Parameter	Conditions		Min	Max	Unit
Per transi	stor					
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
lo	output current			-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \leq 1 ms$		-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		[1]	-	200	mW
	SOT666		[1][2]	-	200	mW
Per device	9					
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		[1]	-	300	mW
	SOT666		<u>[1][2]</u>	-	300	mW
T _{stg}	storage temperature			-65	+150	°C
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT666		<u>[1][2]</u> _	-	625	K/W
Per devie	ce					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		[1][2]	-	416	K/W

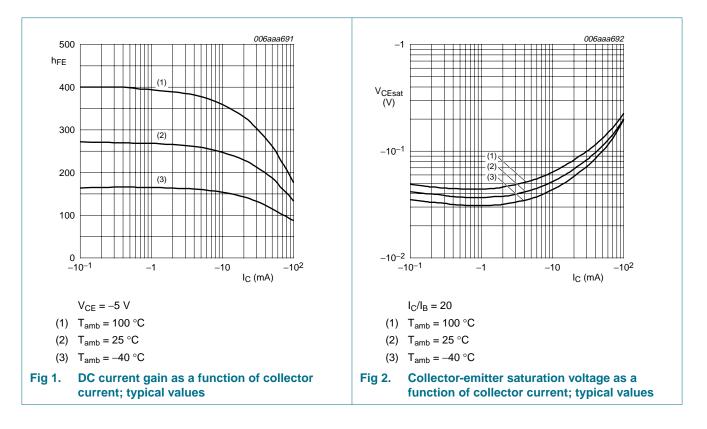
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

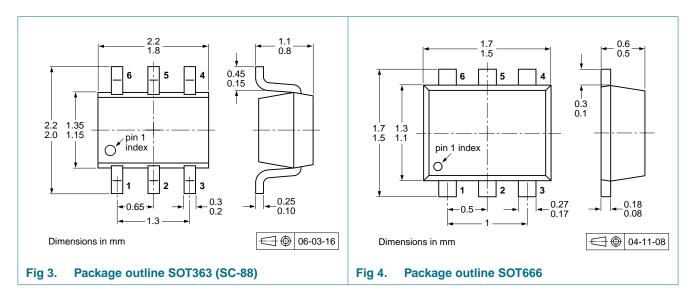
7. Characteristics

Table 8. <i>T_{amb} = 25</i>	Characteristics °C unless otherwise spec	cified.				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter cut-off	V_{CE} = -30 V; I _B = 0 A	-	-	-1	μA
current	$\label{eq:VCE} \begin{array}{l} V_{CE} = -30 \; V; \; I_{B} = 0 \; A; \\ T_{j} = 150 \; ^{\circ}C \end{array}$	-	-	-50	μΑ	
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I_C = -20 mA	30	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -10$ mA; $I_{B} = -0.5$ mA	-	-	-150	mV
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0 \text{ A};$ f = 1 MHz	-	-	3	pF



PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

8. Package outline



9. Packing information

Table 9.Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packi	ng quar	ntity	
			3000	4000	8000	10000
PEMB30	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PUMB30 SOT363		4 mm pitch, 8 mm tape and reel; T1	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	-125	-	-	-165

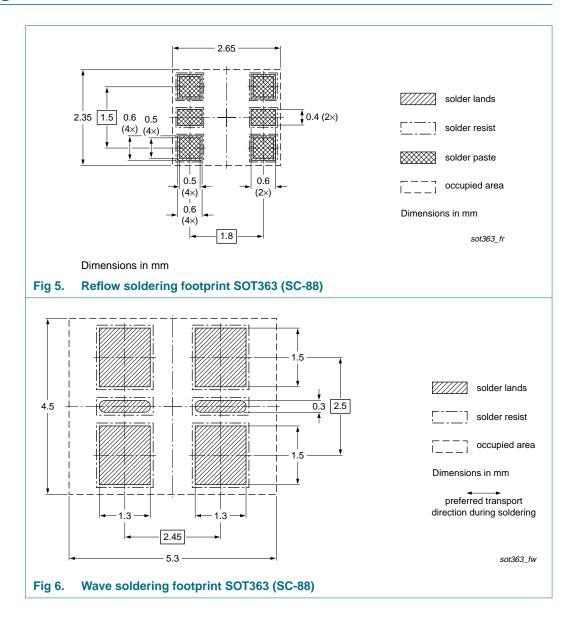
[1] For further information and the availability of packing methods, see Section 13.

[2] T1: normal taping

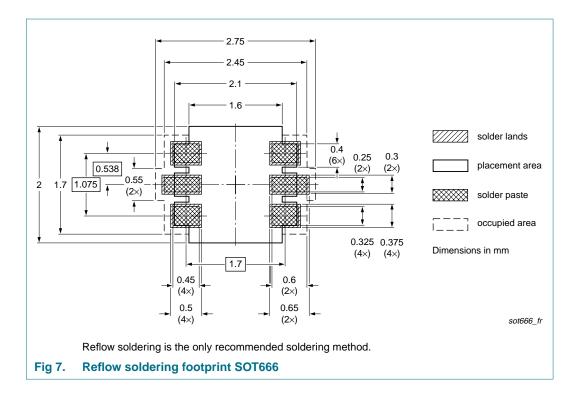
[3] T2: reverse taping

PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

10. Soldering



PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open



PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PEMB30_PUMB30_2	20090902	Product data sheet	-	PEMB30_PUMB30_1		
Modifications:		neet was changed to reflect w legal definitions and disc	• •			
	 Figure 3 "Package outline SOT363 (SC-88)": updated 					
	 Figure 5 "Reflow soldering footprint SOT363 (SC-88)": updated 					
	 Figure 6 "Wave soldering footprint SOT363 (SC-88)": updated 					
	• Figure 7 "R	eflow soldering footprint SC	T666": updated			

PNP/PNP double resistor-equipped transistors; $R1 = 2.2 \text{ k}\Omega$, R2 = open

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

12.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

12.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

13. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

PEMB30_PUMB30_2
Product data sheet

NXP Semiconductors

PEMB30; PUMB30

PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

14. Contents

1	Product profile 1
1.1	General description
1.2	Features
1.3	Applications 1
1.4	Quick reference data
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 3
6	Thermal characteristics 3
7	Characteristics 4
8	Package outline 5
9	Packing information 5
10	Soldering 6
11	Revision history 8
12	Legal information 9
12.1	Data sheet status 9
12.2	Definitions9
12.3	Disclaimers
12.4	Trademarks 9
13	Contact information 9
14	Contents 10

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2009.

All rights reserved.

For more information, please visit: http://www.nxp.com For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 2 September 2009 Document identifier: PEMB30_PUMB30_2



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - Pre-Biased category:

Click to view products by NXP manufacturer:

Other Similar products are found below :

RN1607(TE85L,F) DTA124GKAT146 DTA144WETL DTA144WKAT146 DTC113EET1G DTC115TETL DTC115TKAT146 DTC124TETL DTC144ECA-TP DTC144VUAT106 MUN5241T1G BCR158WH6327XTSA1 NSBA114TDP6T5G NSBA143ZF3T5G NSBC114YF3T5G NSBC123TF3T5G SMUN5235T1G SMUN5330DW1T1G SSVMUN5312DW1T2G RN1303(TE85L,F) RN4605(TE85L,F) TTEPROTOTYPE79 DDTC114EUAQ-7-F EMH15T2R SMUN2214T3G SMUN5335DW1T1G NSBC114TF3T5G NSBC143ZPDP6T5G NSVMUN5113DW1T3G SMUN5230DW1T1G SMUN5133T1G SMUN2214T1G DTC114EUA-TP NSBA144EF3T5G NSVDTA114EET1G 2SC2223-T1B-A 2SC3912-TB-E SMUN5237DW1T1G SMUN5213DW1T1G SMUN5114DW1T1G SMUN2111T1G NSVDTC144EM3T5G DTC124ECA-TP DTC123TM3T5G DTA114ECA-TP DTA113EM3T5G DCX115EK-7-F DTC113EM3T5G NSVMUN5135DW1T1G NSVMUN2237T1G